

(19) World Intellectual Property Organization
International Bureau



(43) International Publication Date
20 February 2003 (20.02.2003)

PCT

(10) International Publication Number
WO 03/015123 A3

(51) International Patent Classification⁷: **H01J 37/32**

(21) International Application Number: PCT/US02/25223

(22) International Filing Date: 8 August 2002 (08.08.2002)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
60/311,050 8 August 2001 (08.08.2001) US
10/032,279 31 December 2001 (31.12.2001) US

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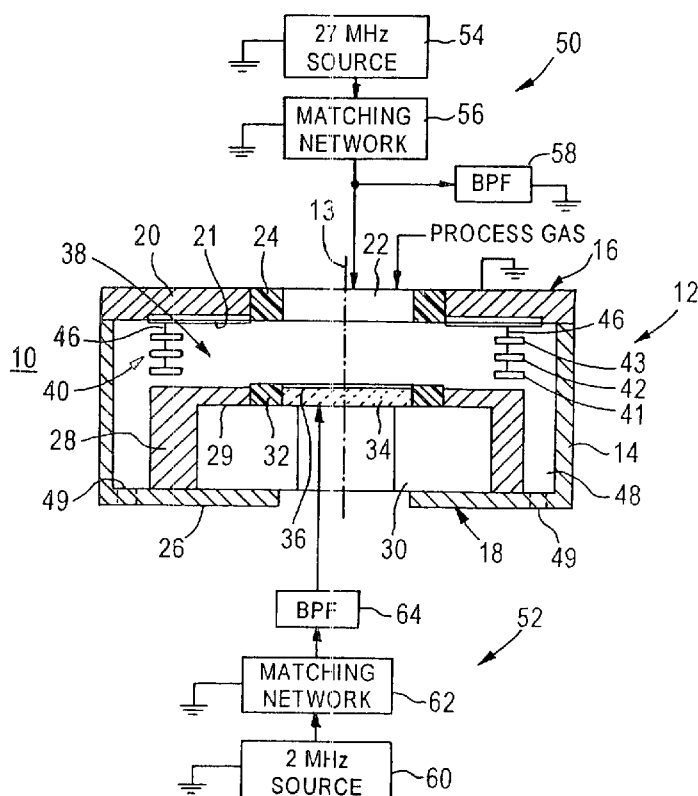
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(81) Designated States (*national*): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, PH, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, TZ, UA, UG, US, UZ, VN, YU, ZA, ZW.

(84) Designated States (*regional*): ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW),

[Continued on next page]

(54) Title: DUAL FREQUENCY PLASMA ETCH REACTOR WITH INDEPENDENT PLASMA DENSITY/CHEMISTRY AND ION ENERGY CONTROL



(57) Abstract: A vacuum plasma chamber for processing a workpiece includes first and second electrodes for electrical coupling with gas in the chamber and respectively connected to first and second relatively high and low frequency RF sources. The chamber includes a wall at a reference potential and a plasma confinement region spaced from the wall. A filter arrangement connected to the sources and the electrodes enables current from the first source to flow to the first electrode, prevents the substantial flow of current from the first source to the second electrode and the second source, and enables current from the second source to flow to the first and second electrodes and prevents the substantial flow of current from the second source to the first source.

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Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),
European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE,
ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, SK,
TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ,
GW, ML, MR, NE, SN, TD, TG).

Published:

- with international search report
- with amended claims

(88) Date of publication of the international search report:

25 September 2003

Date of publication of the amended claims: 20 November 2003

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.